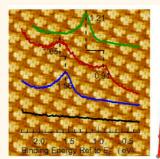
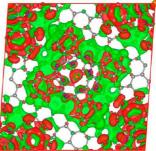
# Energy Level Realignment in Weakly Interacting Donor—Acceptor Binary Molecular Networks

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ABSTRACT Understanding the effect of intermolecular and molecule—substrate interactions on molecular electronic states is key to revealing the energy level alignment mechanism at organic—organic heterojunctions or organic—inorganic interfaces. In this paper, we investigate the energy level alignment mechanism in weakly interacting donor—acceptor binary molecular superstructures, comprising copper hexadecafluorophthalocyanine (F<sub>16</sub>CuPc) intermixed with copper phthalocyanine (CuPc), or manganese phthalocynine (MnPc) on graphite. The molecular electronic structures have been systematically





studied by *in situ* ultraviolet photoelectron spectroscopy (UPS) and low-temperature scanning tunneling microscopy/spectroscopy (LT-STM/STS) experiments and corroborated by density functional theory (DFT) calculations. As demonstrated by the UPS and LT-STM/STS measurements, the observed unusual energy level realignment (*i.e.*, a large downward shift in donor HOMO level and a corresponding small upward shift in acceptor HOMO level) in the  $CuPc - F_{16}CuPc$  binary superstructures originates from the balance between intermolecular and molecule—substrate interactions. The enhanced intermolecular interactions through the hydrogen bonding between neighboring CuPc and  $F_{16}CuPc$  can stabilize the binary superstructures and modify the local molecular electronic states. The obvious molecular energy level shift was explained by gap-state-mediated interfacial charge transfer.

**KEYWORDS:** binary molecular superstructures · self-assembly · energy level alignment · gap states · weak intermolecular interactions · ultraviolet photoelectron spectroscopy · scanning tunneling microscopy

mpressive progress has been made on the controlled assembly of various functional molecules into well-ordered superstructures over the past decades, 1 for their potential applications in molecular electronics.<sup>2</sup> Fabrication of these self-assembled molecular superstructures is mainly controlled by the interplay of multiple interactions between the substrate and the adsorbed molecules, including the strong covalent bonding<sup>3,4</sup> and selective and directional noncovalent interactions, such as weak hydrogen bonding<sup>5,6</sup> and van der Waals interactions.<sup>7,8</sup> In particular, it has already been widely demonstrated that the weak hydrogen bonding and van der Waals interactions play essential roles in the formation of various self-assembled two-dimensional

(2D) binary superstructures.<sup>9–13</sup> Most research efforts are mainly focused on the molecular self-assembly process and the fabrication of the novel molecular nanostructures; however, the understanding of the weak intermolecular interactions on the local molecular electronic states is very limited.

Recently, studies have been devoted to the understanding of the importance of weak noncovalent bond interactions on the performance of molecular electronics, 14,15 as well as the effect of weak intermolecular and molecule—substrate interactions on the energy level alignment in different donor—acceptor assemblies. 16–19 For example, Oteyza *et al.* observed the hybridization and charge transfer behavior in binary assemblies of copper

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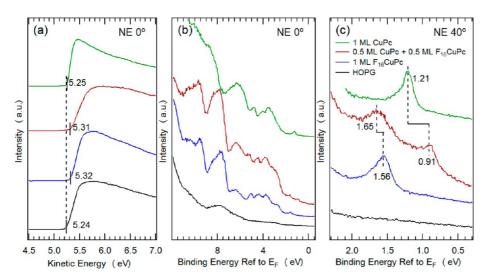


Figure 1. UPS spectra for a CuPc and  $F_{16}$ CuPc monolayer and their 1:1 mixture on a HOPG substrate. (a) UPS spectra at the low-kinetic-energy part with a -5 V sample bias (*i.e.*, secondary electron cutoff), (b) valence band spectra at the low-binding-energy part, and (c) corresponding close-up spectra in the HOMO band region. The photoelectron takeoff angles relative to the analyzer are indicated in the figures (NE  $0^{\circ}$  for photoelectron emission angle of  $0^{\circ}$ , *i.e.*, normal emission, while NE  $40^{\circ}$  for photoelectron emission angle of  $40^{\circ}$ ). All binding energies are relative to the substrate  $E_F$ .

hexadecafluorophthalocyanine (F<sub>16</sub>CuPc) and diindenoperylene (DIP) mediated through molecule-metal interactions. 13,18 To evaluate the molecular energy levels in the donor-acceptor complexes, Cabellos et al. have developed an effective approach to assess the charge transfer behavior in 2D donor-acceptor binary superstructures from X-ray photoelectron spectroscopy (XPS) core level shifts. 19,20 However, many reported self-assembled superstructures were prepared on metal surfaces, which involve relatively strong coupling between the metal d-electrons and the molecular  $\pi$ -orbitals. <sup>18</sup> The existence of interface hybrid electronic states as well as the non-negligible electron "push-back" effect on the metal surface can significantly affect the acquisition of intrinsic valence band information from the ultraviolet photoelectron spectroscopy (UPS) spectra, 21,22 thereby complicating the understanding of the intrinsic energy level alignment at organic donor/acceptor heterojunction interfaces in self-assembled 2D binary superstructures. By using layered inert graphite as substrate, the formation of hybrid interface electronic states can be largely suppressed, thereby serving as an ideal model system to probe the intrinsic molecular electronic states.<sup>23</sup>

In this paper, we investigate the mechanism of weak intermolecular interaction induced energy level realignment in self-assembled binary superstructures at the molecular scale, using model systems of F<sub>16</sub>CuPc intermixed with copper phthalocyanine (CuPc), or manganese phthalocynine (MnPc) on highly oriented pyrolytic graphite (HOPG). The molecular electronic structures were systematically studied through the combination of *in situ* UPS, low-temperature scanning tunneling microscopy/spectroscopy (LT-STM/STS) experiments, and density functional theory (DFT) calculations. We find that the formation of weak

intermolecular hydrogen bonds between neighboring donor and acceptor molecules can significantly perturb the interplay between intermolecular and molecule—substrate interfacial interactions and induce an unusual energy level realignment in self-assembled binary molecular superstructures, mediated through interfacial charge transfer *via* gap states.

# **RESULTS AND DISCUSSION**

To understand the effect of weak hydrogen bonding on the molecular electronic states in self-assembled donor/acceptor binary networks, we first investigated the interfacial electronic structures of CuPc-F<sub>16</sub>CuPc/ HOPG using in situ UPS experiments. Mixed binary superstructures with a CuPc:F<sub>16</sub>CuPc ratio of 1:1 were carefully prepared. 10 Chessboard-like patterns can be formed, steered by the intermolecular C-F···H-C hydrogen bonding between the neighboring CuPc and F<sub>16</sub>CuPc, as reported in our previous STM measurements and molecular dynamic simulations [Figure S1(c) and S1(f)]. 10 Interestingly, the assemblies revealed significant changes in molecular energy levels as shown in Figure 1. The vacuum levels (VL) of all well-ordered monolayers (i.e., CuPc/HOPG, F<sub>16</sub>CuPc/HOPG, binary/ HOPG) were measured by the linear extrapolation of the low-kinetic-energy onset (secondary electron cutoff) of UPS spectra (Figure 1a). Small VL shifts were observed at these interfaces. In particular, at the interface between monolayer  $F_{16}$ CuPc and HOPG, a small upward VL shift of 0.08 eV was observed, suggesting the existence of a weak interfacial charge transfer.<sup>24,25</sup> The degree of the interfacial charge transfer can be roughly estimated from the Helmholtz equation  $^{26,27}$  to be  $\sim$ 0.156 electron per molecule from HOPG to  $F_{16}$ CuPc (details can be found in the Supporting Information).

The valence band evolution is shown in Figure 1b and c. For a single-component monolayer on a HOPG substrate, their highest occupied molecular orbital

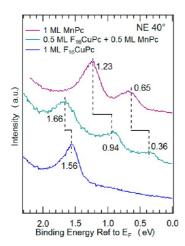


Figure 2. UPS spectra in the HOMO band region for a MnPc and  $F_{16}\text{CuPc}$  monolayer and their 1:1 mixture on a HOPG substrate, respectively. Both the Mn 3d derived HOMO state (0.65 eV) and ligand  $\pi\text{-orbital-induced HOMO state}$  (1.23 eV) shift to the low-binding-energy region by 0.29 eV in the binary network.

(HOMO) peaks are centered at the binding energies of 1.56 eV (F<sub>16</sub>CuPc/HOPG) and 1.21 eV (CuPc/HOPG), respectively. Different HOMO positions as well as the VL evolutions are mainly attributed to their different ionization potentials and can be well understood using the reported gap states model.<sup>28-31</sup> However, the valence band features for the weakly interacting CuPc-F<sub>16</sub>CuPc binary assemblies are not a simple superposition of individual components. As shown by the brown spectrum in Figure 1c, the F<sub>16</sub>CuPc-related HOMO peak slightly shifts to higher binding energy by  $\sim$ 0.09 eV, while the CuPc-related HOMO peak largely shifts to lower binding energy by  $\sim$  0.30 eV and toward the Fermi level ( $E_F$ ). This suggests that the molecular electronic states in the binary superstructures can be significantly perturbed by the local lateral intermolecular interactions between CuPc and F<sub>16</sub>CuPc, even though such interaction is considered to be very weak.  $^{1,16-20,32}$ 

Similar energy level alignments can also be observed in another 2D binary donor/acceptor superstructure of manganese phthalocyanine (MnPc) intermixed with F<sub>16</sub>CuPc (Figure 2). As shown in Figure 2, MnPc is chosen as the donor molecule due to its Mn 3d derived HOMO state,<sup>33</sup> appearing at 0.65 eV below the

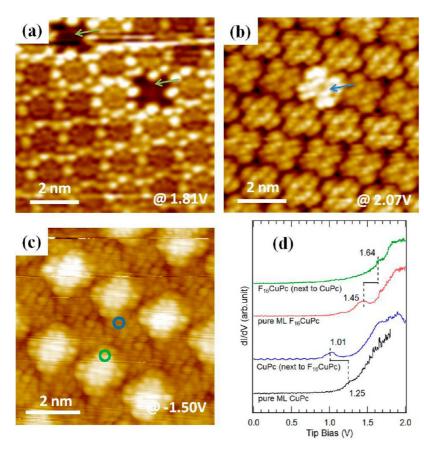


Figure 3. STM images of (a) two  $F_{16}$ CuPc molecules embedded in the CuPc monolayer on HOPG ( $V_{\rm tip}$  = 1.81 V, 10 × 10 nm²; the dark features refer to the  $F_{16}$ CuPc molecules) and (b) one CuPc molecule embedded in the  $F_{16}$ CuPc monolayer on HOPG ( $V_{\rm tip}$  = 2.07 V, 10 × 10 nm²; the bright feature refers to the CuPc molecule). (c) Supramolecular packing structure of CuPc- $F_{16}$ CuPc binary network with intermixing ratio of 2:1. ( $V_{\rm tip}$  = -1.50 V, 8 × 8 nm²; here, the dark and bright features refer to the CuPc and  $F_{16}$ CuPc molecules, respectively). (d) STS spectra taken at the lobe of  $F_{16}$ CuPc molecules and CuPc molecules for both pure and mixed molecular layers.

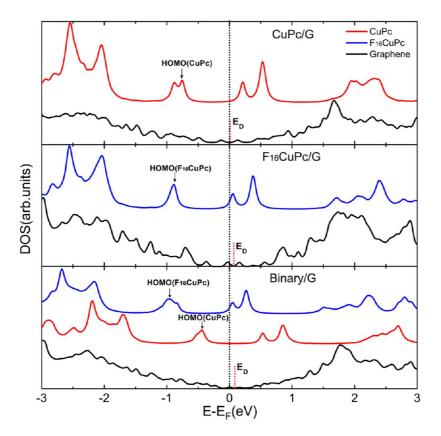


Figure 4. Projected DOS for the monolayer of CuPc, F<sub>16</sub>CuPc, and their 1:1 mixture absorbed on a graphene substrate. The Fermi level is set to zero, and the red dotted lines mark the Dirac point of graphene.

E<sub>F</sub>. The next feature centered at 1.23 eV is assigned to the ligand  $\pi$ -orbital. The evolution of the HOMO levels in the binary assemblies shows a similar trend to that of CuPc-F<sub>16</sub>CuPc, i.e., the MnPc-related HOMOs largely shift toward E<sub>F</sub> by 0.29 eV; in contrast, the F<sub>16</sub>CuPcrelated HOMO again slightly shifts to higher binding energy by 0.10 eV.

To further examine the significant HOMO shift in these well-ordered 2D binary superstructures, we studied the local electronic states of CuPc-F<sub>16</sub>CuPc assemblies on HOPG using in situ LT-STM/STS measurements. As previously reported, both CuPc and F<sub>16</sub>CuPc molecules lie flat on HOPG with their molecular planes parallel to the substrate due to the interfacial  $\pi - \pi$ interaction. 10,34 The packing structures can be well controlled by tuning the relative ratio of the molecules.<sup>9,20</sup> Besides visualizing molecular aggregation and ordering, STM images also provide information on the local surface electronic states of various adsorbates from bias-dependent measurements. 10 In Figure 3a and b, the molecularly resolved STM images reveal the changes of local electronic states of the CuPc-F<sub>16</sub>CuPc assemblies. Figure 3a shows the STM image of two F<sub>16</sub>CuPc molecules embedded into the CuPc monolayer on HOPG. Here, the two darker features are assigned to F<sub>16</sub>CuPc molecules for its deep HOMO state (Figure 1c). Interestingly, the CuPc molecules neighboring the F<sub>16</sub>CuPc appear much brighter than

that of other CuPc molecules, suggesting that their electronic structures have been significantly perturbed by the neighboring F<sub>16</sub>CuPc. By a similar argument, in the STM image shown in Figure 3b, one CuPc molecule (the brighter one) is randomly embedded into the F<sub>16</sub>CuPc monolayer. However, in this case, the local electronic states of the surrounding F<sub>16</sub>CuPc are not obviously affected by the embedded CuPc. The STM results demonstrate that the intrinsic electronic states of CuPc can be significantly modulated in the assemblies, in good agreement with the HOMO level shift as revealed by the UPS measurements shown in Figure 1c; that is, the degree of energy shift for the CuPc HOMO (0.30 eV to lower binding energy region) was much larger than that of F<sub>16</sub>CuPc (0.09 eV to higher binding energy region).

STS measurements were also taken at all these interfaces to measure local electronic density of states (DOS). Figure 3c displays the molecularly resolved STM image of the well-organized CuPc-F<sub>16</sub>CuPc binary network with an intermixing ratio of 2:1. The brighter features here correspond to the F<sub>16</sub>CuPc molecules at negative tip bias. STS spectra were collected at the lobe of each organic molecule as highlighted by the blue and green circles in Figure 3c. The obtained spectra in Figure 3d were averaged over 30 STS spectra taken at similar positions in this binary superstructure. For comparison, the electronic structures of a

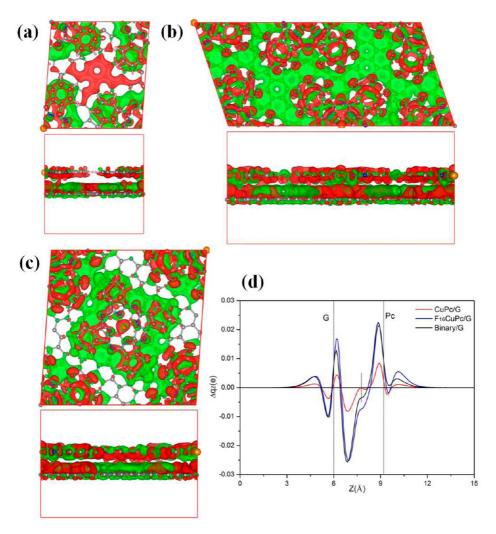


Figure 5. Top view and side view of the charge density difference for (a) CuPc/graphene[(1,5)  $\times$  (4,3)], (b) F<sub>16</sub>CuPc/graphene[(7,8)  $\times$  (2,5)], and (c) binary/graphene[(3,7)  $\times$  (7,3)] at contour levels of 0.002 e/Å. The red and green clouds correspond to regions with electron accumulation and depletion, respectively. (d) One-dimensional charge density difference along the surface normal direction of graphene; vertical lines mark the position of graphene and molecule planes.

single-component monolayer (*i.e.*, CuPc/HOPG, black spectrum;  $F_{16}$ CuPc/HOPG, red spectrum) are also shown in Figure 3d. Clearly, as compared with the single-component monolayer on HOPG, the CuPc-related HOMO peak shifts to lower binding energy by 0.24 eV and the  $F_{16}$ CuPc-related HOMO peak shifts to higher binding energy by 0.19 eV in this binary system. The degree of HOMO state shift differs slightly from the UPS results with a packing structure of 1:1 intermixing ratio, possibly originating from different supramolecular arrangements with different weak intermolecular bonding environments for the localized probing technique.

The UPS and LT-STM/STS results indicate that the local electronic states as well as the energy level alignment in these 2D binary assemblies can be modified by weak intermolecular interactions. We further explored the underlying mechanisms using first-principles calculations for the  $CuPc-F_{16}CuPc$  binary system adsorbed on graphene. During structural

optimization (detailed packing structures can be found in Figure S1), the structures of all adsorbed molecules deviated from their ideal planar structures. For pure CuPc/graphene, the adsorption height for CuPc was 3.26 Å, which was the distance between the lowest Cu atom and graphene (the Cu atom was 0.04 Å lower than all other atoms). Different results were found for  $F_{16}\text{CuPc/graphene}$ , where the F atoms were 0.04 Å lower than the central Cu atom, and the adsorption height was 3.17 Å. For the binary monolayer, the Cu atoms in both CuPc and  $F_{16}\text{CuPc}$  molecules were at the same height of 3.22 Å above the graphene. The molecule adsorption energy was defined as  $^{34}$ 

$$E_{\rm a} = (E_{\rm total} - E_{\rm graphene} - n \times E_{\rm Pc})/n$$

where  $E_{\text{total}}$ ,  $E_{\text{graphene}}$ , and  $E_{\text{Pc}}$  refer to the total energy of the adsorption system, the energy of the isolated graphene substrate, and the energy of gas phase phthalocyanine molecules, respectively, and n is the number of phthalocyanine molecules in the unit cell

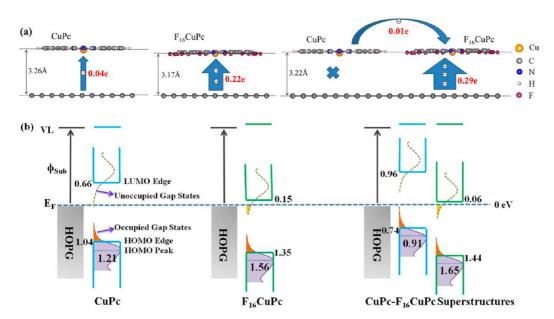


Figure 6. Schematic illustrations of gap-states-mediated weak interface charge transfer behaviors in explaining the significant energy level shift in weakly interacting binary molecular systems. The unoccupied and occupied gap states are indicated by the purple arrows in the figure, which are extended from the LUMO and HOMO edge, respectively, and decayed exponentially into the band gap.

(UC). Long-range dispersion corrections were included in the calculations of the total energies. The calculated adsorption energies for the CuPc,  $F_{16}$ CuPc, and their binary CuPc- $F_{16}$ CuPc monolayers on graphene are  $E_a$ (CuPc) = -2.54 eV/UC,  $E_a$ ( $F_{16}$ CuPc) = -3.06 eV/UC, and  $E_a$ (CuP- $F_{16}$ CuPc) = -2.90 eV/UC, corresponding to 44.6, 53.7, and 50.9 meV/atom, respectively. As previously reported, a dispersion force dominated interfacial interaction can lead to the interaction energy range of 35–60 meV/atom for the phthalocyanine—graphene system. <sup>34,35</sup> Large adsorption heights (~3.22 Å) and small adsorption energies (~50.9 meV/atom) reveal a weak interaction at the binary/graphene interface.

The molecular interface electronic structures of all absorption systems were calculated based on the aforementioned optimized structures (Figure S1). The projected DOS of the adsorbed molecules and graphene substrates are presented in Figure 4. The  $E_{\rm F}$  in all adsorption systems was located below the Dirac point of graphene and shifted toward the lowest unoccupied molecular orbital (LUMO) of the adsorption molecules: E<sub>F</sub> in CuPc/graphene was close to the LUMO of CuPc, while E<sub>F</sub> in F<sub>16</sub>CuPc/graphene almost crossed the LUMO of F<sub>16</sub>CuPc. These results indicate small electron transfer from substrate to molecules. The amount of electron transfer in F<sub>16</sub>CuPc/graphene was larger than that of CuPc/graphene. From the projected DOS, the CuPc-related HOMO shifted 0.28 eV toward E<sub>F</sub> from the CuPc/graphene system to the binary/graphene system, but the F<sub>16</sub>CuPc-related HOMO was shifted 0.05 eV away from  $E_F$ , in good agreement with the experimental results.

In order to gain more insight into the weak electronic interactions between the absorbed molecules and graphene, the corresponding charge density differences (CDD) were also calculated (Figure 5; their corresponding unit cell structure can be seen in Figure S1). The CDD was defined as<sup>34</sup>

$$ho = 
ho_{
m total} - 
ho_{
m Pc} - 
ho_{
m graphene}$$

where  $ho_{
m total}$ ,  $ho_{
m Pc}$ , and  $ho_{
m graphene}$  refer to the charge density of the combined system, isolated phthalocyanine molecule, and graphene with geometries optimized for the adsorption system, respectively. The amount of electron transfer from graphene to phthalocyanine molecules was obtained by integrating the CDD along the surface normal direction z, i.e., 0.04e for CuPc/graphene and 0.22e for F<sub>16</sub>CuPc/graphene, respectively. The results were consistent with the estimations from the Helmholtz equation and the PDOS as displayed in Figure 4 (a much closer  $E_F$  relative to the Dirac point of graphene). One-dimensional CDD shown in Figure 5d also exhibits a relative larger dipole at the F<sub>16</sub>CuPc/graphene interface. Interestingly, for the binary/graphene system, the Bader charge analysis showed 0.01e and 0.28e electron lost in the CuPc molecule and graphene substrate, respectively, while 0.29e electron gained in each F<sub>16</sub>CuPc molecule. Clearly, the electron transfer flow between CuPc and HOPG was changed from receiving 0.04e (CuPc/ graphene) to losing 0.01e (binary/graphene), possibly originating from the perturbation by neighboring F<sub>16</sub>CuPc molecules and the formation of weak intermolecular hydrogen bonding. This change would result in a significant HOMO level shift (toward  $E_F$ ) as shown in the UPS spectra and the PDOS.

The large HOMO level shift ( $\sim$ 0.30 eV) can be well explained using the gap states model (Figure 6; the LUMO was derived from the reported HOMO-LUMO gap<sup>34,36–38</sup>). As previously reported, the density of gap states decays exponentially as a function of energy from the HOMO or LUMO edge, which extends several hundred meV into the band gap.<sup>39</sup> Upon the formation of the binary system, the charge transfer direction between CuPc and graphene was reversed, and hence the  $E_F$  shifted from the bottom of the unoccupied gap states (CuPc/graphene) to the top of the occupied gap states (binary/graphene) in CuPc, thereby inducing a large HOMO shift as observed in Figure 1c and the schematic diagram in Figure 6. F<sub>16</sub>CuPc received more electrons in the binary system. However, because of the large density of gap states near the LUMO edge in F<sub>16</sub>CuPc, the integration of the small range of unoccupied gap states below LUMO was sufficient to accommodate the electrons transferred from HOPG to reach thermodynamic equilibrium (as shown by the schematic in Figure 6), thereby resulting in a small molecular orbital shift, *i.e.*, small HOMO shift observed in Figure 1c.

### CONCLUSION

We have investigated the mechanism of weak intermolecular interaction induced HOMO level shift in selfassembled binary superstructures based on in situ UPS, LT-STM/STS measurements, and first-principles calculations. Our studies elucidated the effects of balanced intermolecular and molecule-substrate interactions on the interface charge transfer behaviors and local electronic states. Although the hydrogen-bonding interactions were demonstrated to be weak by both experimental measurements and DFT calculations, the molecular energy levels can be significantly affected through the gap-states-mediated interfacial charge transfer. Our results can help reveal the importance of weak intermolecular interactions on the molecular electronic states and shed light on exploring and designing new molecular nanostructures with desired functionalities.

### **METHODS**

In situ photoelectron spectroscopy (PES) experiments were carried out in a custom-designed ultrahigh vacuum (UHV) system with a base pressure better than  $2 \times 10^{-10}$  mbar.<sup>40,41</sup> He I $\alpha$  ( $h\nu$  = 21.2 eV) and Mg Ka ( $h\nu$  =1253.6 eV) were used as the excitation sources for UPS and XPS, respectively. Vacuum level shifts were determined from the secondary electron cutoff at the low kinetic energy part of the UPS spectra with a -5 V sample bias. All UPS and XPS measurements were performed at room temperature (RT), and the binding energies of all PES spectra were calibrated and referenced to the Fermi level of a sputter-cleaned Ag(110) substrate. The total instrumental energy resolution was estimated to be about 100 meV for UPS (the energy difference measured between 12% and 88% of the intensity from the Fermi edge of a clean Ag(110) substrate) and 850 meV for XPS (the full width at half-maximum of the Ag 3d peak). The LT-STM/STS experiments were performed in a multichamber UHV system housing an Omicron LT-STM. STM imaging was carried out at 77 K in constant current mode with a chemically etched tungsten tip.

Fresh cleaved HOPG (Mateck/ZYA-grade) substrate was thoroughly degassed in the UHV chamber at around 800 K overnight before molecule deposition. Vacuum-sublimated purified organic molecules were thermally evaporated onto the HOPG substrate at RT from separate Knudsen cells in the growth chamber (base pressure <1  $\times$  10 $^{-9}$  mbar). The deposition rates were monitored by a quartz crystal microbalance during evaporation and were further calibrated by counting the adsorbed molecule coverage in the large-scale STM images at a coverage below 1 monolayer.

Theoretical calculations were performed using VASP code  $^{42-44}$  with the projector-augmented wave (PAW) potentials.  $^{45,46}$  Generalized gradient corrections were applied to the exchange—correlation functional within the implementation of Perdew, Burke, and Ernzerhof (PBE).  $^{47}$  Long-range dispersion corrections were considered within the semiempirical DFT-D2 method.  $^{48}$  After the full convergence test, the kinetic energy cutoff of the plane wave basis was chosen to be 500 eV. Brillouin zones of the superstructures of monolayer CuPc,  $F_{16}$ CuPc, and CuPc— $F_{16}$ CuPc on graphene were sampled in the k-space within the Monkhorst—Pack scheme  $^{49}$  by (4  $\times$  4  $\times$  1),

 $(2 \times 4 \times 1)$ , and  $(4 \times 4 \times 1)$  mesh points, respectively. For geometry optimization, all atomic positions were fully relaxed using the conjugate gradient method when Hellmann—Feynman forces were smaller than 0.02 eV/Å.

Conflict of Interest: The authors declare no competing financial interest.

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Supporting Information Available: Figure S1, STM images and calculated supramolecular packing structures for CuPc,  $F_{16}$ CuPc, and their binary network; Figure S2, atomic structures and the energy levels of the isolated CuPc and  $F_{16}$ CuPc molecules; Figure S3, UPS spectra for MnPc $-F_{16}$ CuPc system; Figure S4, XPS spectra for MnPc $-F_{16}$ CuPc system; Figure S5, UPS spectra in the HOMO band region for CuPc: $F_{16}$ CuPc intermixing ratios of 1:2, 1:1, and 2:1. These materials are available free of charge via the Internet at http://pubs.acs.org.

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